Qualified for Automotive Applications
Wide Input Voltage Range: 3.2V-50V
Low Shutdown Current 3.7uA
Low Quiescent operating Current: 450uA
Adjustable Switching Frequency: 100KHz to 2.2MHz
Integrated Frequency Dithering for EMI Mitigation
External Frequency Synchronic
External Compensation
Supports additional Slope Compensation
22ms Internal Soft-start Time
Integrated Protection Feature

- Constant Peak-Current Protection Threshold Over Input Voltage
- Output Overvoltage Protection
- Adjust Under-Voltage Lockout
- Optional Hiccup Over Load Protection
- Thermal Shutdown Protection:165°C

MSOP-8L(3mm*3mm) Package

Muti-output Flyback
LED Bias Supply
Portable Speaker Supply
Battery Powered Boost/Flyback/SEPIC application

The SCT81620 device is a wide input, non-synchronous boost controller. The Device can be used in Boost, SEPIC and Flyback converters and topologies.

The switching frequency of the SCT81620 device can be adjusted to any value between 100kHz and 2.2MHz by using a single external resistor or by synchronizing it to an external clock. Current mode control provides superior bandwidth and transient response in addition to cycle-by-cycle current limiting.

Over operating free-air temperature range unless otherwise noted

PARAMETER	DEFINITION	MIN	MAX	UNIT
V_{IN}	Input voltage range	3.2	50	V
V_{CC}	VCC voltage range	3.2	6.1	V
T_J	Operating junction temperature	-40	125	°C

PARAMETER	DEFINITION	MIN	MAX	UNIT
V_{ESD}	Human Body Model(HBM), per ANSI-JEDEC-JS-001-2014 specification, all pins	-2	+2	kV
	Charged Device Model(CDM), per ANSI-JEDEC-JS-002-2014specification, all pins	-1	+1	kV

PARAMETER	THERMAL METRIC	MSOP-8	UNIT
R	Junction to ambient thermal resistance(1)	132.8	°C/W

SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
t_{ON_MIN}	Minimum on-time	Fsw=400kHz		250		ns

Protection

V

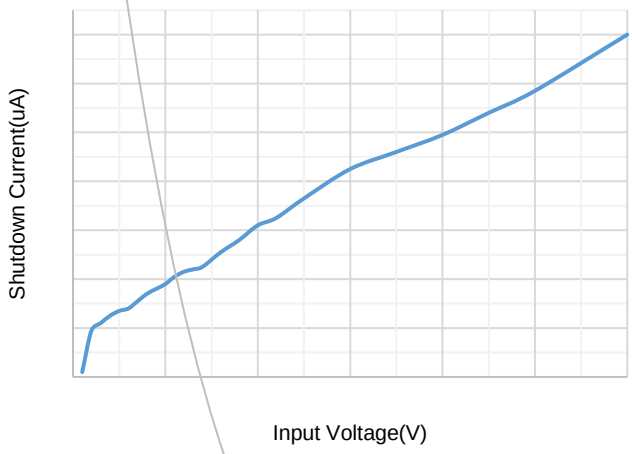


Figure 1. ISD vs Input Voltage

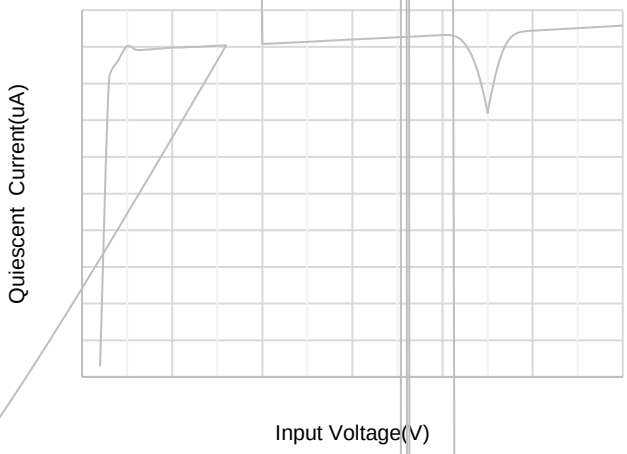


Figure 2. IQ vs Input Voltage

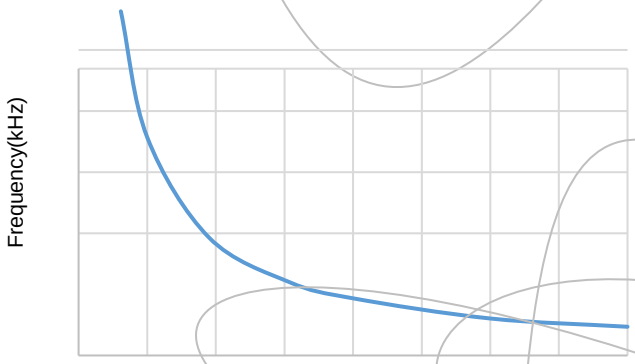


Figure 3. Switching Frequency vs RT

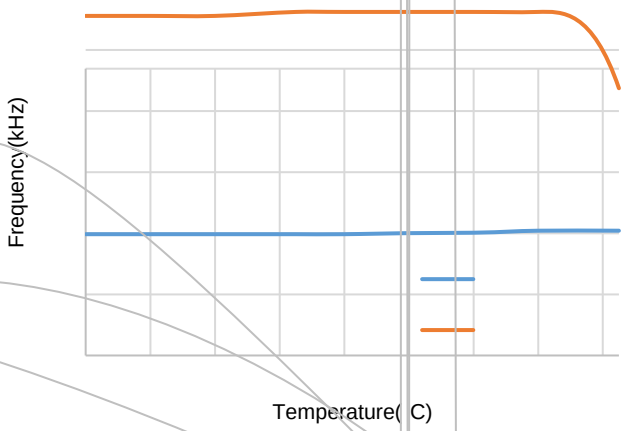


Figure 4. Switching Frequency vs Temperature

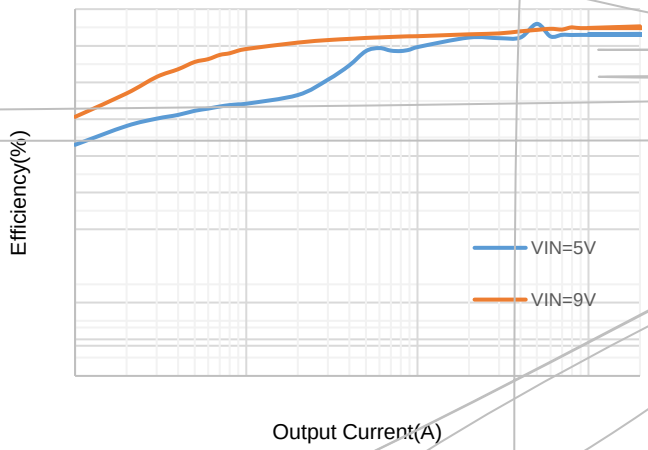


Figure 5. Efficiency vs Load Current, Boost, VOUT=12V

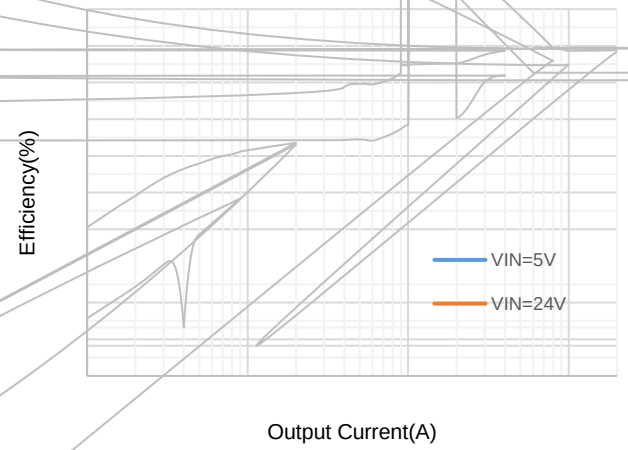


Figure 6. Efficiency vs Load Current, Sepic, VOUT=12V

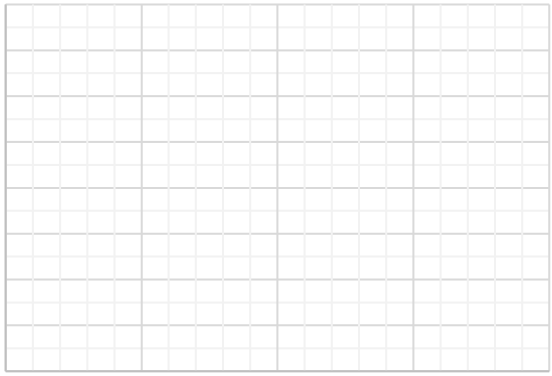


Figure 7. VSENSN vs Input Voltage

Figure 8. DR Volage vs Input Voltage

Figure 9. COMP Current vs Temperature

Figure 10. DR Resistance vs Temperature

Overview

$

Overvoltage Protection

Slope Compensation Ramp

$$V_{samp} \quad I_L * R_{SEN} \tag{1}$$

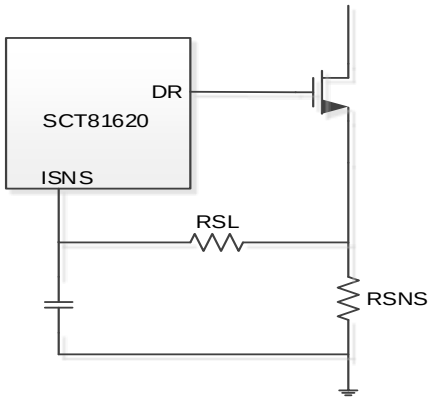


Figure13 .External RSL to increase slope compensation

Adjustable Peak Current Limit

Output Voltage

$$R_{FBT} \quad \frac{V_{OUT} \quad V_{REF}}{V_{REF}} \quad R_{FBB} \tag{12}$$

where:

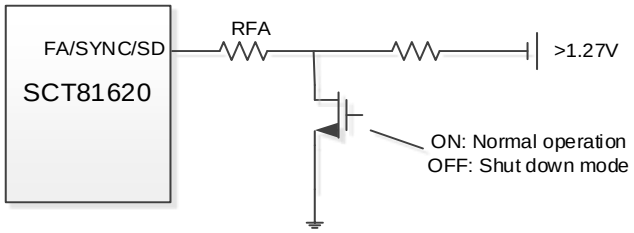


Figure17. Shutdown operation in Frequency Adjust Mode

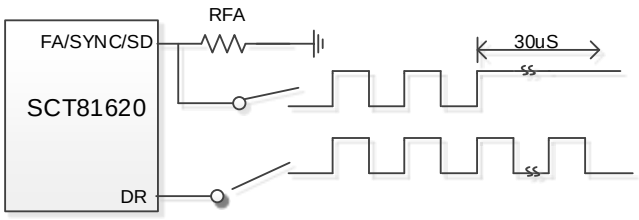


Figure18. Shutdown operation in Frequency Synchronization Mode

Typical Application (Boost)

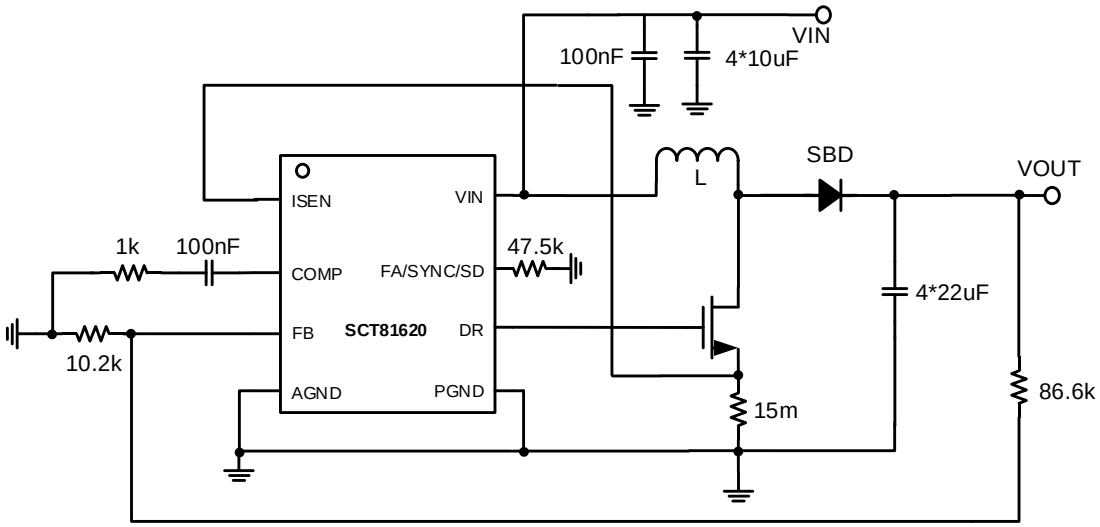


Figure 19. Application Schematic, 3V to 11V, 2A Boost Regulator at 400kHz

Design Parameters

Design Parameters	Example Value
Input Voltage	5V Normal 3V to 11V
Output Voltage	12V
Maximum Output Current	3A
Switching Frequency	400

Where

I_G is the gate drive current.

Output Diode Selection

$$I_{D(PEAK)} \quad \frac{I_{OUT}}{(1 \quad D)} \quad I_L \tag{24}$$

Application Waveforms

Vin=5V, Vout=12V, unless otherwise noted

Figure 20. Power up(Iload=2A)

Figure 21. Power down(Iload=2A)

Figure 22. Over current protection (Iload=5A)

Figure 23. Over

Typical Application (Sepic)

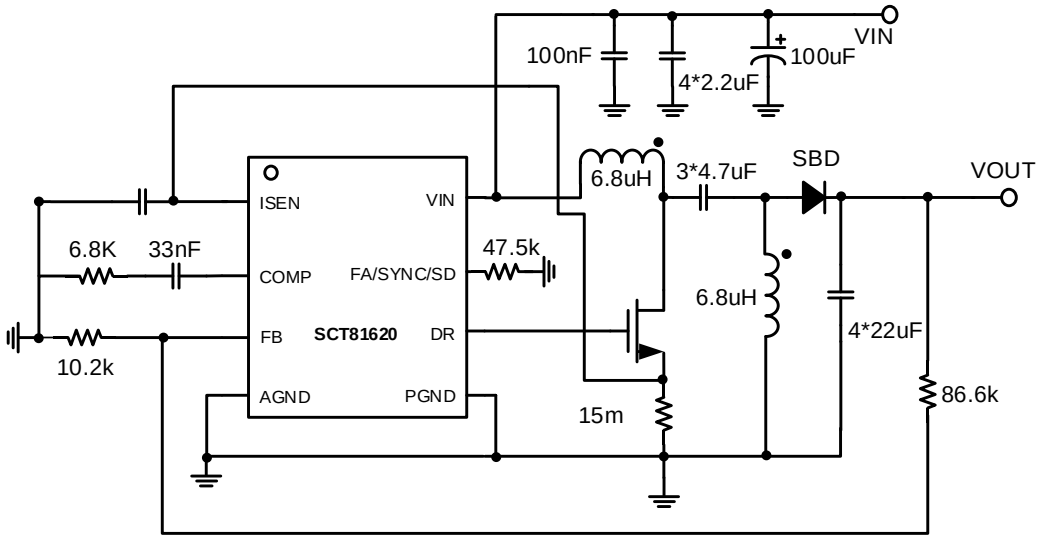


Figure 26. Application Schematic, 5V to 50V, 2A Sepic Regulator at 400kHz

Design Parameters

Design Parameters

Inductor Selection (Sepic)

$$I_{L1} \quad I_{IN} \quad 40\% = I_O \quad \frac{V_O}{V_{IN\_MIN}} \quad 40\% \tag{25}$$

(26)

(27)

f_{SW} is the switching frequency.

$$I_{L1\_PEAK} \quad I_{IN} \quad \frac{I_L}{2} \quad I_O \quad \frac{V_O}{V_{IN\_MIN}} \quad (1 \quad \frac{40\%}{2}) \tag{28}$$

$$I_{L2\_PEAK} \quad I_O \quad \frac{I_L}{2} \quad I_O \quad (1 \quad \frac{40\%}{2}) \tag{29}$$

$$L_1 \quad L_2 \quad \frac{L}{2} = \frac{V_{IN\_MIN}}{2 \quad I_L \quad f_{SW}} \quad D_{MAX} \tag{30}$$

Power MOSFET Selection

$$V_{SW\_PEAK} \quad V_{IN} \quad V_O \quad V_D \tag{31}$$

$$I_{Q\_PEAK} \quad I_{L1\_PEAK} \quad I_{L2\_PEAK} \tag{32}$$

$$I_{Q\_RMS} \quad I_O \quad \sqrt{\frac{V_O \quad V_{IN\_MIN} \quad V_D \quad V_O \quad V_D}{V_{IN\_MIN}^2}} \tag{33}$$

$$P_{DIS} \quad I_{Q\_RMS}^2 \quad R_{DS\_ON} \quad D_{MAX} \quad V_O \quad V_{IN\_MIN} \quad I_{Q\_PEAK} \quad \frac{Q_g \quad f_{SW}}{I_G} \tag{34}$$

I_G is the gate drive current.

Output Diode Selection

$$V_{D\_PEAK} \quad V_{IN\_MAX} \quad V_{O\_MAX} \tag{35}$$

Coupling Capacitor Selection

$$V_{CS} \quad \frac{I_O \quad D_{MAX}}{C_S \quad f_{SW}} \tag{36}$$

$$CS\_RMS \quad O \quad \sqrt{\frac{O \quad D}{IN\_MIN}} \tag{37}$$

Application Waveforms

Vin=5V, Vout=12V, unless otherwise noted

Figure 28. Power up(Iload=2A)

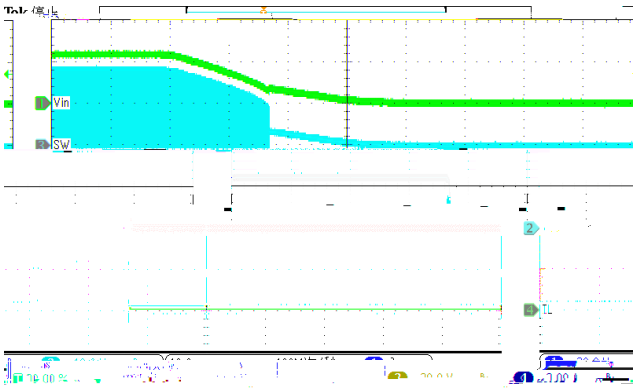


Figure 29. Power down(Iload=2A)

Figure 30. Shutdown remove

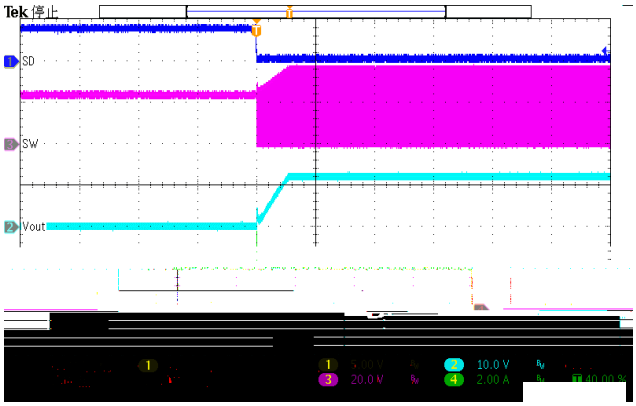


Figure 31. Shutdown remove

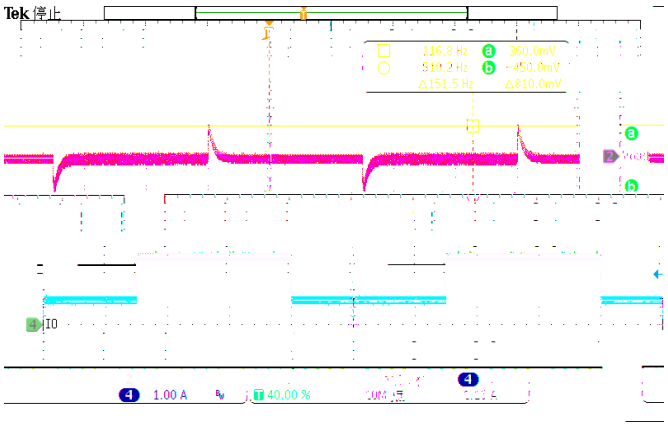


Figure 32. LoadTrans (Iload=0.5A-1.5A)

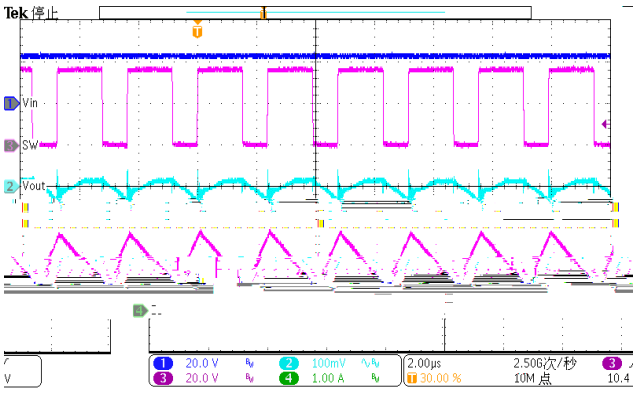
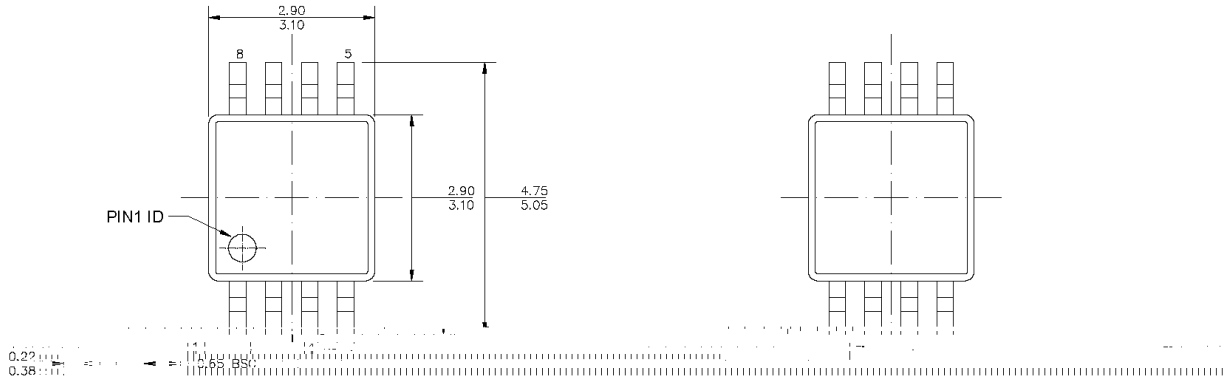


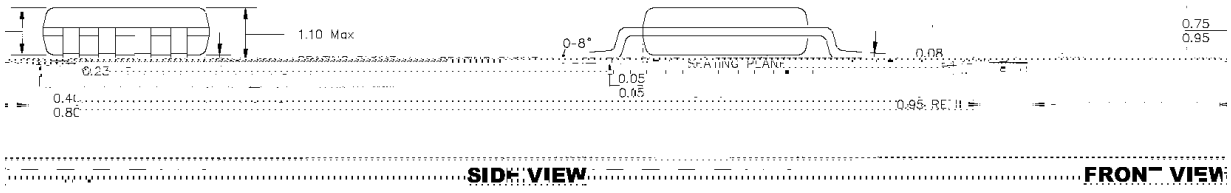
Figure 33. steady-state (Iload=2A)

Layout Guideline

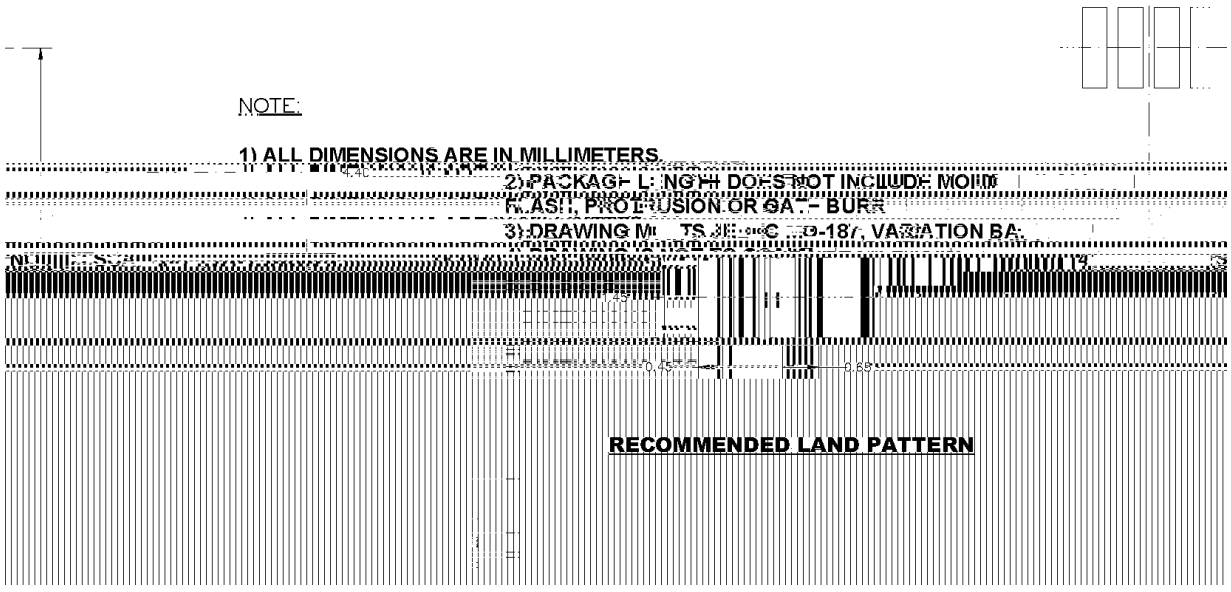
Figure 34. BOOST PCB Layout



TOP VIEW **BOTTOM VIEW**



SIDE VIEW **FRONT VIEW**



RECOMMENDED LAND PATTERN

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